

Thyristor High Voltage, Phase Control SCR, 100 A



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I _{T(AV)}	100 A			
V _{DRM} /V _{RRM}	1200 V			
V _{TM} (typ.)	1.17 V			
I _{GT}	100 mA			
T_J	-40 °C to +150 °C			
Package	TO-247AD 3L			
Circuit configuration	Single SCR			

FEATURES

 AEC-Q101 qualified, meets JESD 201 class 1A whisker test



• 150 °C maximum operating junction temperature COMPLIANT

COMPLIANT HALOGEN FREE

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding, and battery charge.

DESCRIPTION

The VS-100TPS12L high voltage series of silicon controlled rectifiers are specifically designed for medium power switching, and phase control applications. The glass passivation technology used, has reliable operation up to 150 °C junction temperature.

MECHANICAL DATA

Case: TO-247AD 3L

Molding compound meets UL 94 V-0 flammability rating **Terminals:** matte tin plated leads, solderable per

J-STD-002

MAJOR RATINGS AND CHARACTERISTICS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V _{RRM} /V _{DRM}		1200	V
On-state voltage	V _T	100 A, T _J = 125 °C, typical	1.17	V
Average rectified forward current	I _{T(AV)}		100	
Maximum continuous RMS on-state current	I _{RMS}		157	Α
Non-repetitive peak surge current	I _{TSM}	T _J = 150 °C, 10 ms sine	935	
Maximum rate of rise	dV/dt		1000	V/µs
Maximum operating junction and storage temperature range	T _J , T _{Stg}		-40 to +150	°C

VOLTAGE RATINGS				
PART NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	TYP. I _{RRM} /I _{DRM} AT 150 °C mA	
VS-100TPS12L-M3	1200	1300	28	



PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Maximum average on-state current	I _{T(AV)}	T _C = 103 °C, 180° conduction half sine v	wave	-	100	
Maximum continuous RMS on-state current as AC switch	I _{T(RMS)}			-	157	Α
Peak, one-cycle non-repetitive surge current	I	10 ms sine pulse, rated V _{RRM} applied		-	790	
reak, one-cycle non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied	Initial $T_J =$	-	935	
I ² t for fusing	l ² t	10 ms sine pulse, rated V _{RRM} applied	T _J maximum	-	3090	A ² s
1 Clot lusting	1 (10 ms sine pulse, no voltage reapplied		-	4370	8
$I^2\sqrt{t}$ for fusing	I ² √t	t = 0.1 ms to 10 ms, no voltage reapplie	d, T _J = 150 °C	-	43 700	A²√s
		100 A, T _J = 25 °C		1.22	1.37	
On-state voltage	V_{T}	190 A, T _J = 25 °C		1.45	1.61	V
On-state voltage	VT	100 A, T _J = 125 °C		1.17	1.26	
		190 A, T _J = 125 °C		1.47	1.60	
Low level value of threshold voltage	V _{T01}	T _J = 150 °C		-	0.82	V
High level value of threshold voltage	V_{T02}	1j = 150 C		-	0.93	V
Low level value of on-state slope resistance	r _{t1}	T ₁ = 150 °C		-	3.80	mΩ
High level value of on-state slope resistance	r _{t2}	1j = 150 C		-	3.50	11152
Rate of rise of turned-on current	dl/dt	$T_J = 150 ^{\circ}\text{C}$, $V_R < 800 \text{V}$, $I_T = 100 \text{A}$, $I_{gt} = 200 \text{mA}$, $t_r < 100 \text{ns}$, repetitive		-	200	A/µs
Rate of rise of turned-on current	dl/dt	$T_J = 150 ^{\circ}\text{C}$, $V_R < 1000 \text{V}$, $I_T = 100 \text{A}$, $I_{gt} = 200 \text{mA}$, $t_r < 100 \text{ns}$, non repetitive		-	500	A/µs
Holding current	Ι _Η	Anode supply = 6 V, resistive load, T _J = 25 °C		-	300	A
Latching current	ΙL			-	500	mA
		T _J = 25 °C		30	100	μA
Reverse and direct leakage current	I_{RRM}/I_{DRM}	T _J = 125 °C		10	50	mA
		T _J = 150 °C		28	70	
Rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, linear to 80 % V_{DRM} ,	R _{q-k} = open	-	1000	V/µs

TRIGGERING							
PARAMETER	SYMBOL		TEST CONDITIONS	TYP.	MAX.	UNITS	
Peak gate power	P _{GM}	10 ms sino puls	se, no voltage reapplied	-	10	W	
Average gate power	P _{G(AV)}	To mis sine puis	se, no voltage reapplied	-	2.5	VV	
Peak gate current	I _{GM}			-	2.5	Α	
Peak negative gate voltage	-V _{GM}			-	10		
		T _J = -40 °C	Anode supply = 6 V resistive load	1.2	1.7		
Deguired DC gate valtage to trigger	V	T _J = 25 °C	Anode supply = 6 V resistive load	1.0	1.5	V	
Required DC gate voltage to trigger	V _{GT}	T _J = 125 °C	Anode supply = 6 V resistive load	0.7	1.3		
		T _J = 150 °C	Anode supply = 6 V resistive load	0.6	1.1		
		T _J = -40 °C	Anode supply = 6 V resistive load	80	150		
Deguired DC gets to triager		T _J = 25 °C	Anode supply = 6 V resistive load	60			
Required DC gate to trigger	I _{GT}	T _J = 125 °C	Anode supply = 6 V resistive load	25	50	- mA	
		T _J = 150 °C	Anode supply = 6 V resistive load	17	35		
DC gate voltage not to trigger	V_{GD}	T ₁ = 150 °C. V _{DBM} = 80 % rated value		-	0.20	V	
DC gate current not to trigger	I _{GD}			3.0	mA		

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS
Turn-on time	t _{gt}	$I_T = 100 \text{ A}, V_D = 50 \% V_{DRM}, I_{gt} = 300 \text{ mA}, T_J = 25 °C$	1.8	-	
Turn-off time	t _q	$\begin{split} I_T &= 100 \text{ A, V}_D = 80 \text{ \% V}_{DRM}, \text{dV/dt} = 20 \text{ V/}\mu\text{s, t}_p = 200 \mu\text{s} \\ I_{gt} &= 100 \text{ mA, dI/dt} = 10 \text{A/}\mu\text{s, V}_R = 100 \text{V, T}_J = 150 ^{\circ}\text{C} \end{split}$	135	i	μs



△R _{thJ-HS} CONDUCTION PER JUNCTION											
DEVICE	S	INE HALF	-WAVE CO	NDUCTIO	N	REC	CTANGULA	AR WAVE	CONDUCT	ION	UNITS
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-100TPS12L-M3	0.032	0.047	0.042	0.044	0.046	0.030	0.039	0.041	0.044	0.046	°C/W

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	MAX.	UNITS
Maximum operating junction and storage temperature range		T _J , T _{Stg}		-40	150	°C
Maximum thermal resistance, junction to case		R _{thJC}		-	0.25	
Maximum thermal resistance, junction to ambient		R _{thJA}		-	40	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth, and greased	0.	20	
Approximate weight				(6	g
Mounting torque	minimum			6	(5)	kgf · cm
Mounting torque	maximum			12	(10)	(lbf · in)
Marking device			Case style TO-247AD 3L	1	00TPS1	2LH

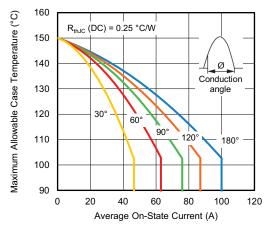


Fig. 1 - Current Rating Characteristics

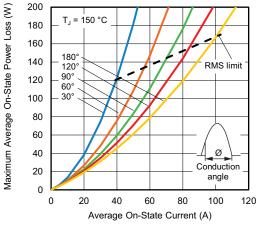


Fig. 3 - On-State Power Loss Characteristics

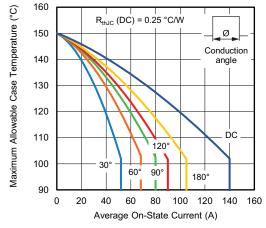


Fig. 2 - Current Rating Characteristics

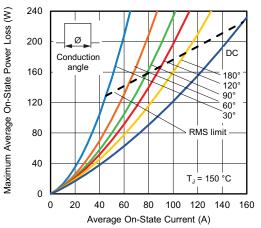


Fig. 4 - On-State Power Loss Characteristic

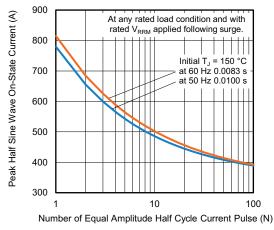


Fig. 5 - Maximum Non-Repetitive Surge Current

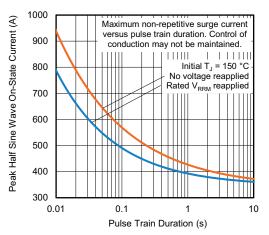


Fig. 6 - Maximum Non-Repetitive Surge Current

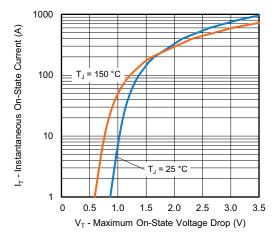


Fig. 7 - On-State Voltage Drop Characteristics

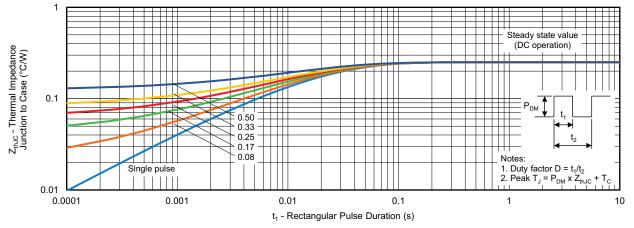
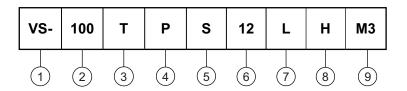


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

- Current code (100 = 100 A)

Circuit configuration:

T = thyristor

4 - P = TO-247 package

5 - Type of silicon:

S = standard recovery rectifier

6 - Voltage code (12 = 1200 V)

7 - Package L = long lead

8 - H = AEC-Q101 qualified

9 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

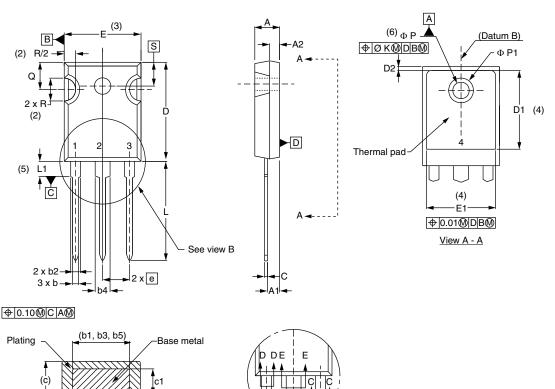
ORDERING INFORMATION (example)				
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION	
VS-100TPS12LHM3	25	500	Antistatic plastic tubes	

LINKS TO RELATED DOCUMENTS		
Dimensions	www.vishay.com/doc?95626	
Part marking information	www.vishay.com/doc?95007	



TO-247AD 3L

DIMENSIONS in millimeters and inches



		Section C -	C, D - D, E -	<u>· E</u>	
SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	

0.039

0.065

0.065

0.102

0.102

0.015

0.015

0.776

0.515

0.053

0.094

0.092

0.135

0.133

0.035

0.033

0.815

(h h2 h4)

:5	

View B

SYMBOL	MILLIMILILIA		INOTILS		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46 BSC		0.215 BSC		
ØΚ	0.254		0.010		
L	19.81	20.32	0.780	0.800	
L1	3.71	4.29	0.146	0.169	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217 BSC		
•	•		•		•

INCHES

MILLIMETERS

Notes

b1

b2

b3

b4

b5

С

с1

D

D1

(1) Dimensioning and tolerancing per ASME Y14.5M-1994

1.35

2.39

2.34

3.43

3.38

0.89

0.84

20.70

- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body

3

- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1

0.99

1.65

1.65

2.59

2.59

0.38

0.38

19.71

13.08

- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4



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